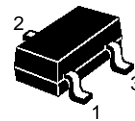


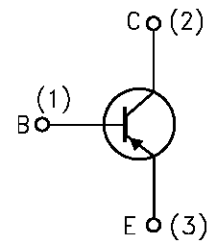
SMALL SIGNAL PNP TRANSISTORS

Type	Marking
SO5401	P33

- SILICON EPITAXIAL PLANAR PNP TRANSISTORS
- MINIATURE PLASTIC PACKAGE FOR APPLICATION IN SURFACE MOUNTING CIRCUITS
- GENERAL PURPOSE AND HIGH VOLTAGE AMPLIFIER


SOT-23

INTERNAL SCHEMATIC DIAGRAM



SC08810

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-160	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-150	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_{CM}	Collector Peak Current	-0.6	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	200	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

SO5401

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	620	$^{\circ}\text{C}/\text{W}$
R_{thj-SR} •	Thermal Resistance Junction-Substrate	Max	400	$^{\circ}\text{C}/\text{W}$

• Mounted on a ceramic substrate area = 7 x 5 x 0.5 mm

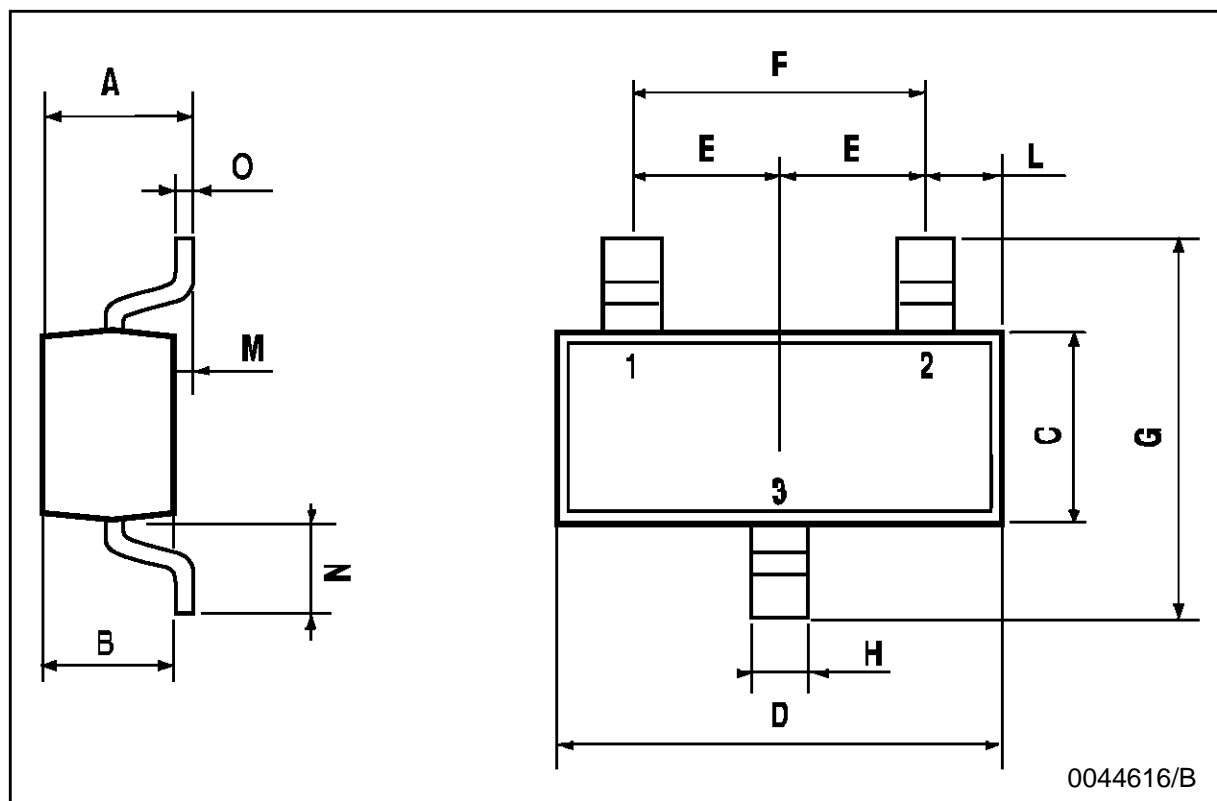
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = -120\text{ V}$			-50	nA
I_{EBO}	Collector Cut-off Current ($I_C = 0$)	$V_{EB} = -3\text{ V}$			-50	nA
$V_{(BR)CBO}^*$	Collector-Emitter Breakdown Voltage ($I_E = 0$)	$I_C = -100\ \mu\text{A}$	-160			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = -1\text{ mA}$	-150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_C = -10\text{ nA}$	-5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = -10\text{ mA}$ $I_B = -1\text{ mA}$ $I_C = -50\text{ mA}$ $I_B = -5\text{ mA}$			-0.2 -0.5	V V
$V_{BE(sat)}^*$	Collector-Base Saturation Voltage	$I_C = -10\text{ mA}$ $I_B = -1\text{ mA}$ $I_C = -50\text{ mA}$ $I_B = -5\text{ mA}$			-1 -1	V V
h_{FE}^*	DC Current Gain	$I_C = -1\text{ mA}$ $V_{CE} = -5\text{ V}$ $I_C = -10\text{ mA}$ $V_{CE} = -5\text{ V}$ $I_C = -50\text{ mA}$ $V_{CE} = -5\text{ V}$	50 60 50	240		
f_T	Transition Frequency	$I_C = -10\text{ mA}$ $V_{CE} = -10\text{ V}$ $f = 1\text{ MHz}$	100		400	MHz
C_{CB}	Collector Base Capacitance	$I_E = 0$ $V_{CE} = -10\text{ V}$ $f = 1\text{ MHz}$			6	pF
NF	Noise Figure	$V_{CE} = -5\text{ V}$ $I_C = -0.25\text{ mA}$ $f = 1\text{ KHz}$ $\Delta f = 200\text{ Hz}$ $R_G = 1\text{ K}\Omega$		5		dB
h_{fe}^*	Small Signal Current Gain	$V_{CE} = -5\text{ V}$ $I_C = -1\text{ mA}$ $f = 1\text{ KHz}$	40		200	

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



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